

Fast Recovery Epitaxial Diode (FRED)

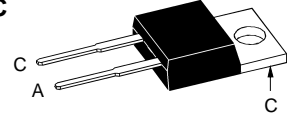
DSEI 12

$I_{FAVM} = 11 A$
 $V_{RRM} = 1200 V$
 $t_{rr} = 50 ns$

V_{RSM}	V_{RRM}	Type
V	V	
1200	1200	DSEI 12-12A



TO-220 AC



A = Anode, C = Cathode

Symbol	Test Conditions	Maximum Ratings	
I_{FRMS}	$T_{VJ} = T_{VJM}$	25	A
I_{FAVM} ①	$T_C = 100^\circ C$; rectangular, $d = 0.5$	11	A
I_{FRM}	$t_p < 10 \mu s$; rep. rating, pulse width limited by T_{VJM}	150	A
I_{FSM}	$T_{VJ} = 45^\circ C$; $t = 10 ms$ (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	75	A
		80	A
	$T_{VJ} = 150^\circ C$; $t = 10 ms$ (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	65	A
		70	A
I^2t	$T_{VJ} = 45^\circ C$; $t = 10 ms$ (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	28	A ² s
		27	A ² s
	$T_{VJ} = 150^\circ C$; $t = 10 ms$ (50 Hz), sine $t = 8.3 ms$ (60 Hz), sine	21	A ² s
		20	A ² s
T_{VJ}		-40...+150	°C
T_{VJM}		150	°C
T_{stg}		-40...+150	°C
P_{tot}	$T_C = 25^\circ C$	78	W
M_d	Mounting torque	0.4...0.6	Nm
Weight		2	g

Features

- International standard package JEDEC TO-220 AC
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Symbol	Test Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ C$		250 μA
	$T_{VJ} = 25^\circ C$	$V_R = V_{RRM}$	150 μA
	$T_{VJ} = 125^\circ C$	$V_R = 0.8 \cdot V_{RRM}$	4 mA
V_F	$I_F = 12 A$; $T_{VJ} = 150^\circ C$ $T_{VJ} = 25^\circ C$		2.2 V
			2.6 V
V_{T0}	For power-loss calculations only		1.65 V
r_T	$T_{VJ} = T_{VJM}$		46.2 mΩ
R_{thJC}	0.5		1.6 K/W
R_{thCK}			K/W
R_{thJA}			60 K/W
t_{rr}	$I_F = 1 A$; $-di/dt = 50 A/\mu s$; $V_R = 30 V$; $T_{VJ} = 25^\circ C$	50	70 ns
I_{RM}	$V_R = 540 V$; $I_F = 12 A$; $-di_F/dt = 100 A/\mu s$ $L \leq 0.05 \mu H$; $T_{VJ} = 100^\circ C$	6.5	7.2 A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle $d = 0.5$
 Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

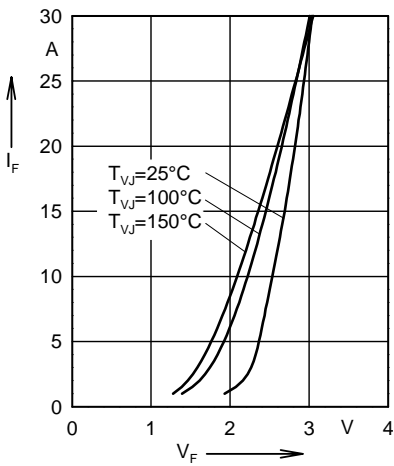


Fig. 1 Forward current versus voltage drop.

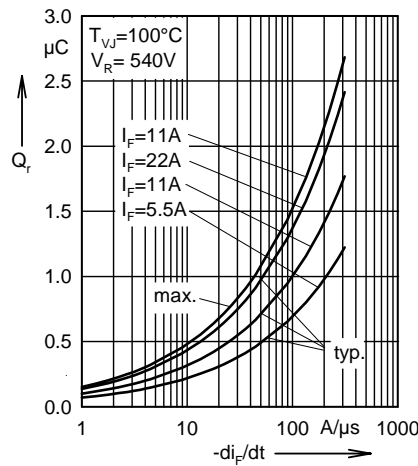


Fig. 2 Recovery charge versus $-di_F/dt$.

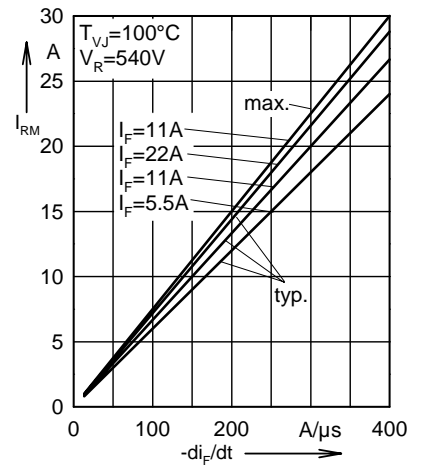


Fig. 3 Peak reverse current versus $-di_F/dt$.

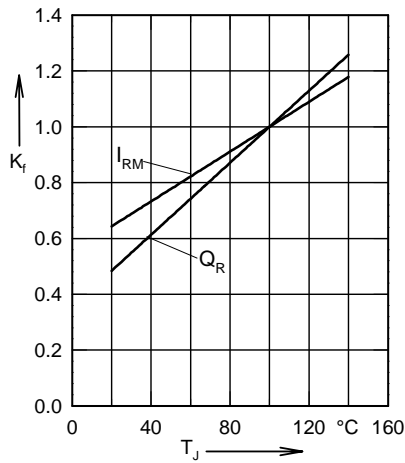


Fig. 4 Dynamic parameters versus junction temperature.

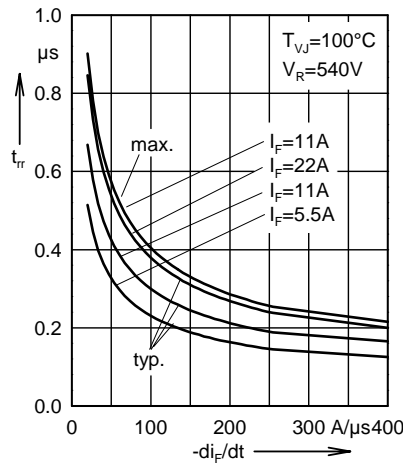


Fig. 5 Recovery time versus $-di_F/dt$.

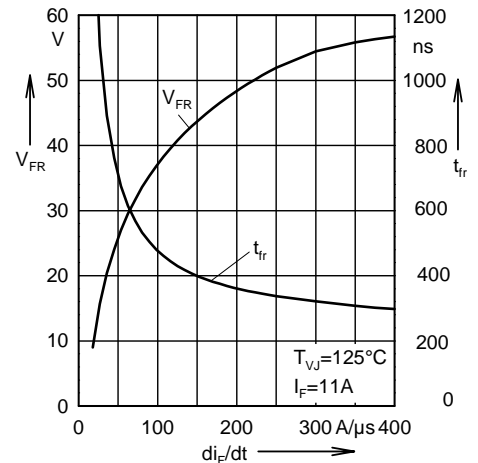


Fig. 6 Peak forward voltage versus di_F/dt .

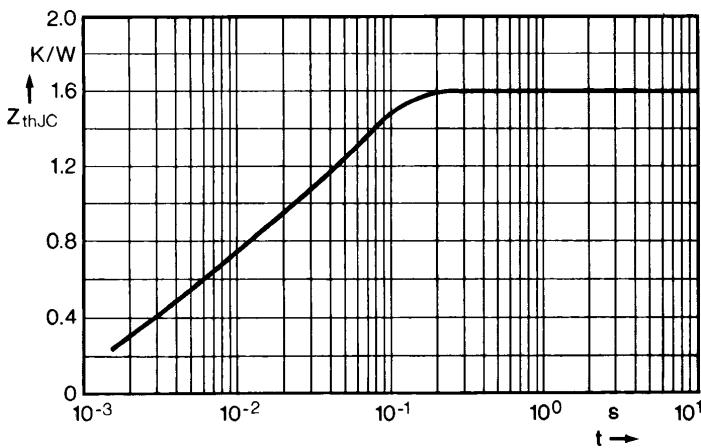
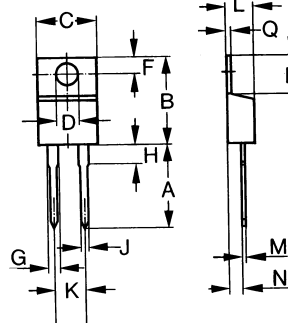


Fig. 7 Transient thermal impedance junction to case.

Dimensions



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	14.73	0.500	0.580
B	14.23	16.51	0.560	0.650
C	9.66	10.66	0.380	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.420
F	2.54	3.42	0.100	0.135
G	1.15	1.77	0.045	0.070
H	-	6.35	-	0.250
J	0.64	0.89	0.025	0.035
K	4.83	5.33	0.190	0.210
L	3.56	4.82	0.140	0.190
M	0.38	0.56	0.015	0.022
N	2.04	2.49	0.080	0.115
Q	0.64	1.39	0.025	0.055